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AMENDMENT TRANSMITTAL LETTER

Docket No. M4065.0159/P159-A

Application	No
09/902.69	91

Filing Date July 12, 2001 Examiner P. Brock

Art Unit 2815

Applicant((s):	Li Li,	et al.

Invention: METHOD OF CONTROLLING SRIATIONS AND CD LOSS IN CONTACT OXIDE ETCH

TO THE COMMISSIONER FOR PATENTS

Transmitted herewith is an amendment in the above-identified application.

The fee has been calculated and is transmitted as shown below.

		CLAIM	S AS AMENI	DED				
	Claims Remaining After Amendment	Highest Number Previously Paid	Number Extra Claims Present	ı	Rate			
Total Claims	28	- 26 =	1	x	18.00)	36.00)
ndependent Claims	2	- 3 =		х			0.00)
Multiple Depend	dent Claims (ch	eck if applicabl	e)					
Other fee (pleas	e specify):							
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Large Entity				S	mall En	tity		
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The Commis as described	ssioner is here! d below. A dup ny overpaymer any additio n at all	oy authorized to dicate copy of the	o charge and this sheet is e	enclosed	l.			
Thomas J. D'Ar Attorney Reg. N				C	Dated:	Septemb	er 26, 200)2
2101 L Street N	C 20037-1526		Y LLP				SEP 3	

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Approved for use through 10/31/2002. OMB 0651-0032 U.S. Patent and Trademark Office; U.S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it displays a valid OMB control number. Complete if Known FEE TRANSMITTAL 09/902,691 Application Number July 12, 2001 for FY 2002 Filing Date First Named Inventor Li Li P. Brock **Examiner Name** 7R40000 cant claims small entity status. See 37 CFR 1.27 2815 Group Art Unit M4065.0159/P159-A TOTAL AMOUNT OF PAYMENT 36.00 Attorney Docket No. FEE CALCULATION (continued) METHOD OF PAYMENT (check all that apply) Credit Money 3. ADDITIONAL FEES Check Х Other None Deposit Account Large Entity Small Entity Deposit 04-1073 **Fee Description** Code (\$) Code (\$) Fee Paid Number Deposit Dickstein Shapiro Morin & 105 130 205 65 Surcharge - late filing fee or oath Oshinsky LLP Name Surcharge - late provisional filing fee or cover 127 50 227 25 The Commissioner is hereby authorized to: (check all that apply) sheet. Charge fee(s) indicated below X Credit any overpayments 139 130 139 130 Non-English specification Charge any additional fee(s) during the pendency of this 147 2.520 147 2,520 For filing a request for ex parte reexamination Requesting publication of SIR prior to 9201 112 9201 112 Charge fee(s) indicated below, except for the filing fee Examiner action Requesting publication of SIR after to the above-identified deposit account. 113 1,840 113 1,840* Examiner action **FEE CALCULATION** 115 110 215 55 Extension for reply within first month 216 200 Extension for reply within second month 1. BASIC FILING FEE 116 400 217 Extension for reply within third month Large Entity **Small Entity** 117 920 460 Fee Fee 118 1,440 218 720 Extension for reply within fourth month Fee Description Code (\$) Code (\$) Fee Paid Utility filing fee 128 1.960 228 980 Extension for reply within fifth month 101 740 201 370 106 330 206 165 Design filing fee 119 320 219 160 Notice of Appeal 107 510 207 255 Plant filing fee 120 320 220 160 Filing a brief in support of an appeal 221 108 740 208 370 Reissue filing fee 121 280 140 Request for oral hearing Petition to institute a public use proceeding 138 1.510 Provisional filing fee 138 1.510 114 160 214 240 Petition to revive - unavoidable 140 110 55 SUBTOTAL (1) (\$) 0.00 1.280 241 640 Petition to revive - unintentional 141 142 1.280 242 640 Utility issue fee (or reissue) 2. EXTRA CLAIM FEES FOR UTILITY AND REISSUE 143 460 243 230 Design issue fee Fee Paid Claims below 36.00 2**8** 620 244 310 Plant issue fee 2 18.00 144 Total Claims -26** = Independent Petitions to the Commissioner 122 130 122 130 -3** = 0.00 123 50 123 50 Processing fee under 37 CFR 1.17(q) Multiple Dependent 126 180 126 180 Submission of Information Disclosure Stmt Small Entity Large Entity Recording each patent assignment per 581 40 581 40 **Fee Description** (\$) Code (\$) property (times number of properties) Code Filing a submission after final rejection 103 18 203 9 Claims in excess of 20 740 246 370 146 (37 ČFR 1.129(a)) 202 102 84 42 Independent claims in excess of 3 For each additional invention to be 740 249 370 149 280 204 Multiple dependent claim, if not paid examined (37CFR 1.129(b)) 104 140 279 Request for Continued Examination (RCE) 109 209 42 ** Reissue independent claims 179 740 370 84 over original patent Request for expedited examination 169 900 169 900 Reissue claims in excess of 20 of a design application 110 210 9 18 and over original patent Other fee (specify) SUBTOTAL (2) (\$) 0.00 36.00 *Reduced by Basic Filing Fee Paid SUBTOTAL (3) (\$) **or number previously paid, if greater; For Reissues, see above Complete (if applicable) SUBMITTED BY

egistration No. 28,371 Telephone (202) 828-2232 Name (Print/Type) Thomas J. D'Amico (Attorney/Agent) Date September 26, 2002 Signature

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Docket No.: M4065.0159/P159-A

(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:

Li Li, et al.

Application No.: 09/902,691

Group Art Unit: 2815

Filed: July 12, 2001

Examiner: P. Brock

For: METHOD OF CONTROLLING

STRIATIONS AND CD LOSS IN

CONTACT OXIDE ETCH

AMENDMENT

Box Non-Fee Amendment

Commissioner for Patents Washington, DC 20231

Dear Sir:

In response to the Office Action dated June 26, 2002 (Paper No. 4), please amend the above-identified U.S. Patent application as follows:

In the Claims:

Please rewrite claim 59 as shown in the Replacement Claims.

Please add the following new claims:

92. (New) An integrated circuit substrate formed by a method comprising the steps of:

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(a) placing said integrated circuit substrate into a reactive chamber;

- (b) introducing an etching gas into said chamber;
- (c) generating a plasma of said etching gas at a first power level and contacting

said substrate with said first power level plasma for a first predetermined time; and

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